

TOSHIBA THYRISTOR SILICON PLANAR TYPE

SF3GZ47, SF3JZ47

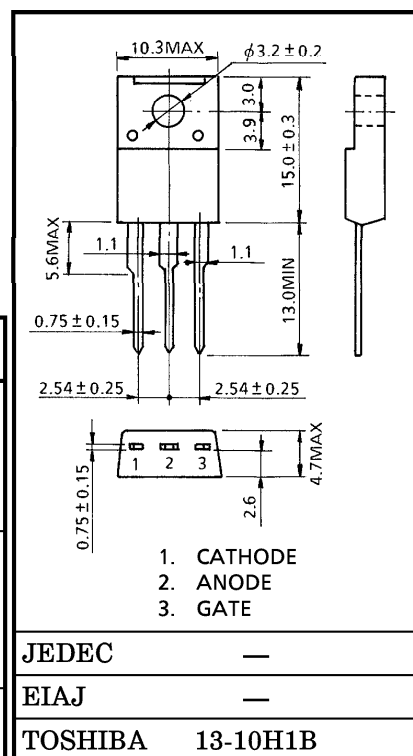
MEDIUM POWER CONTROL APPLICATIONS

Unit in mm

- Repetitive Peak Off-State Voltage : V_{DRM}
- Repetitive Peak Reverse Voltage : V_{RRM} } = 400, 600V
- Average On-State Current : $I_T(AV) = 3A$
- Isolation Voltage : $V_{Isol} = 1500V AC$

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	SF3GZ47	V_{DRM}	400	V
	SF3JZ47	V_{RRM}	600	
Non-Repetitive Peak Reverse Voltage (Non-Repetitive < 5ms, $T_j = 0 \sim 125^\circ C$)	SF3GZ47	V_{RSM}	500	V
	SF3JZ47		720	
Average On-State Current (Half Sine Waveform $T_c = 98^\circ C$)		$I_T(AV)$	3	A
R.M.S On-State Current		$I_T(RMS)$	4.7	A
Peak One Cycle Surge On-State Current (Non-Repetitive)		I_{TSM}	50 (50Hz)	A
			55 (60Hz)	
I^2t Limit Value		I^2t	18	A^2s
Critical Rate of Rise of On-State Current (Note 1)		di/dt	100	$A/\mu s$
Peak Gate Power Dissipation		P_{GM}	5	W
Average Gate Power Dissipation		$P_G(AV)$	0.5	W
Peak Forward Gate Voltage		V_{FGM}	10	V
Peak Reverse Gate Voltage		V_{RGM}	-5	V
Peak Forward Gate Current		I_{GM}	2	A
Junction Temperature		T_j	-40~125	$^\circ C$
Storage Temperature Range		T_{stg}	-40~150	$^\circ C$
Isolation Voltage (AC, $t = 1min.$)		V_{Isol}	1500	V



Note 1 : di/dt Test Condition, $V_{DRM} = 0.5 \times \text{Rated}$, $I_{TM} \leq 12A$, $t_{gw} \geq 10\mu s$, $t_{gr} \leq 250ns$,
 $i_{gp} = I_{GT} \times 2.0$

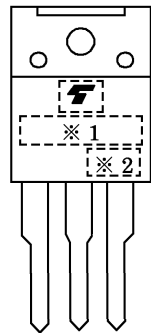
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	I_{DRM} I_{RRM}	$V_{\text{DRM}} = V_{\text{RRM}} = \text{Rated}$	—	—	10	μA
Peak On-State Voltage	V_{TM}	$I_{\text{TM}} = 12\text{A}$	—	—	1.5	V
Gate Trigger Voltage	V_{GT}	$V_{\text{D}} = 6\text{V}, R_{\text{L}} = 10\Omega$	—	—	1.0	V
Gate Trigger Current	I_{GT}		—	—	10	mA
Gate Non-Trigger Voltage	V_{GD}	$V_{\text{D}} = \text{Rated} \times 2 / 3, T_{\text{c}} = 125^{\circ}\text{C}$	0.2	—	—	V
Critical Rate of Rise of Off-State Voltage	dv / dt	$V_{\text{DRM}} = \text{Rated}, T_{\text{c}} = 125^{\circ}\text{C}$ Exponential Rise	—	50	—	$\text{V} / \mu\text{s}$
Holding Current	I_{H}	$V_{\text{D}} = 6\text{V}, I_{\text{TM}} = 1\text{A}$	—	—	40	mA
Latching Current	I_{L}	$V_{\text{D}} = 6\text{V}, f = 50\text{Hz}, t_{\text{gw}} = 50\mu\text{s}$ $i_{\text{G}} = 30\text{mA}$	—	—	50	mA
Thermal Resistance	$R_{\text{th (j-c)}}$	Junction to Case	—	—	4.5	$^{\circ}\text{C} / \text{W}$

MARKING



※1	MARK	F3GZ47	TYPE NAME	SF3GZ47
		F3JZ47		SF3JZ47
※2	Lot Number		Example	
	□ □ Month (Starting from Alphabet A) Year (Last Decimal Digit of the Current Year)		8A : January 1998 8B : February 1998 8L : December 1998	

